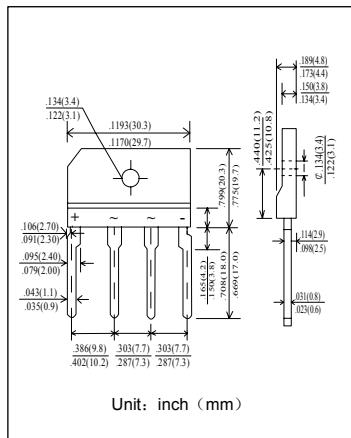




Single-phase Silicon Bridge Rectifier

## D6SB20 THRU D6SB80

Reverse Voltage 200 to 800 V  
Forward Current 6.0A



### 特征 Features

- 低的反向漏电流 Low reverse leakage
- 较强的正向浪涌承受能力 High forward surge capability
- 浪涌承受能力: 170 A Surge overload rating: 170 Amperes peak

### 机械数据 Mechanical Data

- 封装: 塑料封装 Case: Molded Plastic
- 极性: 标记模压或印于本体 Polarity: Symbols molded or marked on body
- 安装位置: 任意 Mounting Position: Any
- 重量: 4.6 克 Weight: 4.6 Grams

**极限值和温度特性** TA = 25°C 除非另有规定。

**Maximum Ratings & Thermal Characteristics** Ratings at 25°C ambient temperature unless otherwise specified.

	符号 Symbols	D6SB20	D6SB40	D6SB60	D6SB80	单位 Unit
最大可重复峰值反向电压 Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	200	400	600	800	V
最大均方根电压 Maximum RMS voltage	V <sub>RMS</sub>	140	280	420	560	V
最大直流阻断电压 Maximum DC blocking voltage	V <sub>DC</sub>	200	400	600	800	V
最大正向平均整流电流 加散热片 T <sub>C</sub> = 111°C Maximum average forward rectified current 无散热片 T <sub>A</sub> = 25°C	I <sub>F(AV)</sub>	6.0				A
峰值正向浪涌电流 8.3ms单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave	I <sub>FSM</sub>	170				A
最大反向峰值电流 @TA = 75°C Maximum peak reverse current full cycle	I <sub>R(AV)</sub>	30				μA
典型热阻 Typical thermal resistance	R <sub>θJA</sub>	6				°C/W
工作结温和存储温度 Operating junction and storage temperature range	T <sub>j</sub> , T <sub>TSG</sub>	-50 --- +150				°C

**电特性** TA = 25°C 除非另有规定。

**Electrical Characteristics** Ratings at 25°C ambient temperature unless otherwise specified.

	符号 Symbols	D6SB20	D6SB40	D6SB60	D6SB80	单位 Unit
最大正向电压 Maximum forward voltage	I <sub>F</sub> = 3.0A	V <sub>F</sub>	1.05			V
最大反向电流 Maximum reverse current	TA = 25°C	I <sub>R</sub>	10			μA
典型结电容 Type junction capacitance	V <sub>R</sub> = 4.0V, f = 1MHz	C <sub>j</sub>	40			pF

**D6SB20 THRU D6SB80**

 Reverse Voltage 200 to 800 V  
 Forward Current 6.0A

**Characteristic Curves**
